

Vaclav Holy

List of Publications by Year in descending order

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365
papers

9,520
citations

70961

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82
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371
all docs

371
docs citations

371
times ranked

8663
citing authors

#	ARTICLE	IF	CITATIONS
1	The surface degradation and its impact on the magnetic properties of bulk VI3. Materials Chemistry and Physics, 2022, 278, 125590.	2.0	7
2	Energetic Au ion beam implantation of ZnO nanopillars for optical response modulation. Journal Physics D: Applied Physics, 2022, 55, 215101.	1.3	2
3	Microstructural modifications induced in Si⁺-implanted yttria-stabilised zirconia: a combined RBS-C, XRD and Raman investigation. Physical Chemistry Chemical Physics, 2022, 24, 6290-6301.	1.3	0
4	V-pits formation in InGaN/GaN: influence of threading dislocations and indium content. Journal Physics D: Applied Physics, 2022, 55, 255101.	1.3	3
5	Single-crystal studies and electronic structure investigation of the room-temperature semiconductor NaMnAs. Physical Review B, 2022, 105, .	1.1	1
6	Effect of pulse laser frequency on PLD growth of LuFeO3 explained by kinetic simulations of in-situ diffracted intensities. Scientific Reports, 2022, 12, 5647.	1.6	2
7	Crystal structure evolution in the van der Waals vanadium trihalides. Journal of Physics Condensed Matter, 2022, 34, 294007.	0.7	5
8	Time-Resolved Morphology and Kinetic Studies of Pulsed Laser Deposition-Grown Pt Layers on Sapphire at Different Growth Temperatures by <i>in Situ</i> Grazing Incidence Small-Angle X-ray Scattering. Langmuir, 2021, 37, 734-749.	1.6	3
9	Strain relaxation in InGaN/GaN epilayers by formation of V-pit defects studied by SEM, XRD and numerical simulations. Journal of Applied Crystallography, 2021, 54, 62-71.	1.9	6
10	As-doped SnSe single crystals: Ambivalent doping and interaction with intrinsic defects. Physical Review B, 2021, 103, .	1.1	7
11	In situ grazing-incidence x-ray scattering study of pulsed-laser deposition of Pt layers. Physical Review B, 2020, 102, .	1.1	2
12	Nanostructures in various Au ion-implanted ZnO facets modified using energetic O ions. Physical Chemistry Chemical Physics, 2020, 22, 23563-23573.	1.3	8
13	Entropy-controlled fully reversible nanostructure formation of Ge on miscut vicinal Si(001) surfaces. Physical Review B, 2020, 102, .	1.1	3
14	Structure Quality of LuFeO3 Epitaxial Layers Grown by Pulsed-Laser Deposition on Sapphire/Pt. Materials, 2020, 13, 61.	1.3	5
15	Watching nanomaterials with X-ray eyes: Probing different length scales by combining scattering with spectroscopy. Progress in Materials Science, 2020, 112, 100667.	16.0	21
16	X-ray diffraction reveals the amount of strain and homogeneity of extremely bent single nanowires. Journal of Applied Crystallography, 2020, 53, 1310-1320.	1.9	3
17	Evolution of $\hat{\Gamma}_2$ phase in metastable $\hat{\Gamma}_2$ titanium alloys studied by small-angle X-ray scattering. MATEC Web of Conferences, 2020, 321, 12039.	0.1	0
18	Effective algorithm for simulations of layer-by-layer growth during pulsed-laser deposition. Physical Review E, 2020, 102, 063305.	0.8	3

#	ARTICLE	IF	CITATIONS
19	Anomalous X-ray diffraction from TiO_2 nanoparticles in Ti^{2+} -Ti(Mo) single crystals. Acta Crystallographica Section A: Foundations and Advances, 2019, 75, 718-729.	0.0	1
20	Influence of an Anomalous Temperature Dependence of the Phase Coherence Length on the Conductivity of Magnetic Topological Insulators. Physical Review Letters, 2019, 123, 036406.	2.9	13
21	Ferroelectric Self-Poling in GeTe Films and Crystals. Crystals, 2019, 9, 335.	1.0	22
22	High power factor and mobility of single crystals of Bi_2Se_3 induced by Mo doping. Journal of Solid State Chemistry, 2019, 277, 819-827.	1.4	7
23	Composition of TiO_2 -Phase Particles in Ti(Mo) Alloys Studied by Anomalous X-ray Diffraction. Crystals, 2019, 9, 440.	1.0	3
24	Study of thermal recrystallisation in Si implanted by 0.4 MeV heavy ions. Surface and Interface Analysis, 2019, 51, 1113-1120.	0.8	1
25	In situ detection of stability limit of TiO_2 phase in Ti^{15}Mo alloy during heating. Journal of Applied Crystallography, 2019, 52, 1061-1071.	1.9	7
26	Indium Incorporation into InGaN Quantum Wells Grown on GaN Narrow Stripes. Materials, 2019, 12, 2583.	1.3	6
27	Distinct defect appearance in Gd implanted polar and nonpolar ZnO surfaces in connection to ion channeling effect. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 061406.	0.9	5
28	Interplay between Structural and Thermoelectric Properties in Epitaxial $\text{Sb}_{2+x}\text{Te}_{3-y}$ Alloys. Advanced Functional Materials, 2019, 29, 1805184.	7.8	25
29	Vacancies in SnSe single crystals in a near-equilibrium state. Physical Review B, 2019, 99, .	1.1	33
30	Rapid floating zone growth of Ni_2MnGa single crystals exhibiting magnetic shape memory functionality. Journal of Alloys and Compounds, 2019, 775, 533-541.	2.8	11
31	Crystal structures and phase transitions of the van der Waals ferromagnet $\sqrt{3}\sqrt{3}\sqrt{3}$ $\text{Rb}_2\text{Mg}_3\text{Cl}_9$. Physical Review Materials, 2019, 3, 011101.	0.9	33
32	Density of bunched threading dislocations in epitaxial GaN layers as determined using X-ray diffraction. Journal of Applied Physics, 2018, 123, .	1.1	16
33	Self-Seeded Axio-Radial $\text{InAs}_{1-x}\text{P}_x$ Nanowire Heterostructures beyond Common VLS Growth. Nano Letters, 2018, 18, 144-151.	4.5	15
34	Thermoelectric and magnetic properties of Cr-doped single crystal Bi_2Se_3 – Search for energy filtering. Journal of Solid State Chemistry, 2018, 258, 768-775.	1.4	14
35	Local moment formation and magnetic coupling of Mn dopants in Bi_2Se_3 : A low-temperature ferromagnetic resonance study. Physica B: Condensed Matter, 2018, 536, 604-613.	1.3	4
36	Diffuse X-ray scattering from local chemical inhomogeneities in InGaN layers. Journal of Applied Crystallography, 2018, 51, 969-981.	1.9	5

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37	Structural disorder of natural Bi_2Te_3 superlattices grown by molecular beam epitaxy. <i>Physical Review Materials</i> , 2018, 2, .	0.9	10
38	High-resolution x-ray diffraction of epitaxial bismuth chalcogenide topological insulator layers. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2017, 8, 015006.	0.7	7
39	Structure of epitaxial SrIrO_3 perovskite studied by interference between X-ray waves diffracted by the substrate and the thin film. <i>Journal of Applied Crystallography</i> , 2017, 50, 385-398.	1.9	11
40	Kinetic Monte Carlo simulation of growth of Ge quantum dot multilayers with amorphous matrix. <i>Journal of Nanoparticle Research</i> , 2017, 19, 1.	0.8	2
41	Twin domain imaging in topological insulator Bi_2Te_3 and Bi_2Se_3 epitaxial thin films by scanning X-ray nanobeam microscopy and electron backscatter diffraction. <i>Journal of Applied Crystallography</i> , 2017, 50, 369-377.	1.9	28
42	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	6
43	Magnetic properties of the CrMnFeCoNi high-entropy alloy. <i>Physical Review B</i> , 2017, 96, .	1.1	124
44	Magnetic anisotropy in antiferromagnetic hexagonal MnTe. <i>Physical Review B</i> , 2017, 96, .	1.1	49
45	Interband absorption edge in the topological insulators Bi_2Te_3 and Bi_2Se_3 . <i>Physical Review B</i> , 2017, 96, .	1.1	12
46	Characterization of individual stacking faults in α -GaAs nanowire by nanobeam X-ray diffraction. <i>Journal of Synchrotron Radiation</i> , 2017, 24, 981-990.	1.0	9
47	On the completeness of the β to α transformation in metastable β titanium alloys. <i>Journal of Applied Crystallography</i> , 2017, 50, 283-287.	1.9	11
48	Introduction to the special issue on high-resolution X-ray diffraction and imaging. <i>Journal of Applied Crystallography</i> , 2017, 50, 671-672.	1.9	0
49	Topological insulator homojunctions including magnetic layers: The example of n-p type (n-QLs) $\text{Bi}_2\text{Te}_3/\text{Bi}_2\text{Se}_3$ junctions. <i>Physical Review B</i> , 2017, 95, 040401.	1.5	5
50	SrAl_2O_9 thin films by chemical solution deposition and their use as buffer layers for oriented growth of hexagonal ferrites. <i>Thin Solid Films</i> , 2016, 616, 228-237.	0.8	1
51	Structure and microstructure of Ni-Mn-Ga single crystal exhibiting magnetic shape memory effect analysed by high resolution X-ray diffraction. <i>Acta Materialia</i> , 2016, 115, 250-258.	3.8	22
52	Ferroelectric phase transitions in multiferroic $\text{Ge}_1-x\text{Mn}_x\text{Te}$ driven by local lattice distortions. <i>Physical Review B</i> , 2016, 94, .	1.1	13
53	Strain-induced nonsymmorphic symmetry breaking and removal of Dirac semimetallic nodal line in an orthoperovskite iridate. <i>Physical Review B</i> , 2016, 93, .	1.1	67
54	Electronic and transport properties of the Mn-doped topological insulator Bi_2Te_3 . A first-principles study. <i>Physical Review B</i> , 2016, 93, .	1.1	16

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55	Ultrafast changes of magnetic anisotropy driven by laser-generated coherent and noncoherent phonons in metallic films. <i>Physical Review B</i> , 2016, 93, .	1.1	38
56	Contributions from coherent and incoherent lattice excitations to ultrafast optical control of magnetic anisotropy of metallic films. , 2016, , .		0
57	Disentangling bulk and surface Rashba effects in ferroelectric GeTe . <i>Physical Review B</i> , 2016, 94, .	1.1	74
58	Multiple-stable anisotropic magnetoresistance memory in antiferromagnetic MnTe . <i>Nature Communications</i> , 2016, 7, 11623.	5.8	169
59	The instrumental resolution of a moire extensometer in light of its recent automatisation. <i>Measurement: Journal of the International Measurement Confederation</i> , 2016, 91, 258-265.	2.5	16
60	Nonmagnetic band gap at the Dirac point of the magnetic topological insulator $(\text{Bi}_{1-x}\text{Mn}_x)_2\text{Se}_3$. <i>Nature Communications</i> , 2016, 7, 10559.	5.8	102
61	Magnetic and structural properties of Mn-doped Bi_2Se_3 topological insulators. <i>Physica B: Condensed Matter</i> , 2016, 481, 262-267.	1.3	18
62	Current-induced torques in structures with ultrathin IrMn antiferromagnets. <i>Physical Review B</i> , 2015, 92, .	1.1	46
63	Self-assembly of Ge quantum dots on periodically corrugated Si surfaces. <i>Applied Physics Letters</i> , 2015, 107, 203101.	1.5	5
64	The electronic structure of homogeneous ferromagnetic $(\text{Ga}, \text{Mn})\text{N}$ epitaxial films. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	11
65	Structural investigations of the Si_{12}Ge superstructure. <i>Journal of Applied Crystallography</i> , 2015, 48, 262-268.	1.9	3
66	Giant reversible nanoscale piezoresistance at room temperature in Sr_2IrO_4 thin films. <i>Nanoscale</i> , 2015, 7, 3453-3459.	2.8	24
67	Production of three-dimensional quantum dot lattice of Ge/Si core-shell quantum dots and Si/Ge layers in an alumina glass matrix. <i>Nanotechnology</i> , 2015, 26, 065602.	1.3	16
68	Three-dimensional reciprocal space mapping with a two-dimensional detector as a low-latency tool for investigating the influence of growth parameters on defects in semipolar GaN. <i>Journal of Applied Crystallography</i> , 2015, 48, 1000-1010.	1.9	8
69	X-ray diffraction strain analysis of a single axial $\text{InAs}_{1-x}\text{P}_x$ nanowire segment. <i>Journal of Synchrotron Radiation</i> , 2015, 22, 59-66.	1.0	8
70	Powder diffraction in Bragg-Brentano geometry with straight linear detectors. <i>Journal of Applied Crystallography</i> , 2015, 48, 613-618.	1.9	35
71	Optical and magneto-optical studies of martensitic transformation in Ni-Mn-Ga magnetic shape memory alloys. <i>Journal of Applied Physics</i> , 2015, 117, 17A919.	1.1	9
72	Structural and electronic properties of manganese-doped Bi_2Te_3 epitaxial layers. <i>New Journal of Physics</i> , 2015, 17, 013028.	1.2	33

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73	kinetics of TiO_2 particles in Ti matrix studied by small-angle X-ray scattering. <i>Acta Materialia</i> , 2014, 81, 71-82.	3.8	13
74	Single crystal growth of TIMETAL LCB titanium alloy by a floating zone method. <i>Journal of Crystal Growth</i> , 2014, 405, 92-96.	0.7	17
75	Structure and composition of bismuth telluride topological insulators grown by molecular beam epitaxy. <i>Journal of Applied Crystallography</i> , 2014, 47, 1889-1900.	1.9	36
76	A complex study of the fast blue luminescence of oxidized silicon nanocrystals: the role of the core. <i>Nanoscale</i> , 2014, 6, 3837.	2.8	38
77	Interaction between graphene and copper substrate: The role of lattice orientation. <i>Carbon</i> , 2014, 68, 440-451.	5.4	180
78	Ordered array of TiO_2 particles in Ti matrix studied by small-angle X-ray scattering. <i>Acta Materialia</i> , 2014, 81, 71-82.	3.8	30
79	Crystallization kinetics study of cerium titanate CeTi_2O_6 . <i>Journal of Physics and Chemistry of Solids</i> , 2014, 75, 265-270.	1.9	14
80	$\text{Fe}_2\text{O}_3/\text{TiO}_2$ nanoparticles—a complex structural study. <i>Thin Solid Films</i> , 2014, 564, 65-72.	0.8	3
81	Influence of a low-temperature capping on the crystalline structure and morphology of InGaN quantum dot structures. <i>Journal of Alloys and Compounds</i> , 2014, 585, 572-579.	2.8	5
82	Self-ordering of iron oxide nanoparticles covered by graphene. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 2499-2504.	0.7	2
83	Ge quantum dot lattices in Al_2O_3 multilayers. <i>Journal of Nanoparticle Research</i> , 2013, 15, 1.	0.8	27
84	Picosecond inverse magnetostriction in galfenol thin films. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	52
85	Growth, Structure, and Electronic Properties of Epitaxial Bismuth Telluride Topological Insulator Films on BaF_2 (111) Substrates. <i>Crystal Growth and Design</i> , 2013, 13, 3365-3373.	1.4	70
86	Growth of TiO_2 inclusions in Ti alloys: An X-ray diffraction study. <i>Acta Materialia</i> , 2013, 61, 6635-6645.	3.8	20
87	Tetragonal phase of epitaxial room-temperature antiferromagnet CuMnAs . <i>Nature Communications</i> , 2013, 4, 2322.	5.8	123
88	Reverse micelles directed synthesis of TiO_2 – CeO_2 mixed oxides and investigation of their crystal structure and morphology. <i>Journal of Solid State Chemistry</i> , 2013, 198, 485-495.	1.4	26
89	Magnetostrictive thin films for microwave spintronics. <i>Scientific Reports</i> , 2013, 3, 2220.	1.6	73
90	Study of threading dislocation density reduction in AlGaN epilayers by Monte Carlo simulation of high-resolution reciprocal-space maps of a two-layer system. <i>Journal of Applied Crystallography</i> , 2013, 46, 120-127.	1.9	13

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91	Growth of a three-dimensional anisotropic lattice of Ge quantum dots in an amorphous alumina matrix. Journal of Applied Crystallography, 2013, 46, 709-715.	1.9	8
92	Unit cell structure of the wurtzite phase of GaP nanowires: X-ray diffraction studies and density functional theory calculations. Physical Review B, 2013, 88, .	1.1	28
93	Growth and characterization of stacking fault reduced GaN $(1,0,ar\{1,3\})$ on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308.	1.3	12
94	Three-dimensional reciprocal space mapping of diffuse scattering for the study of stacking faults in semipolar $(1\bar{1}02)$ GaN layers grown from the sidewall of an $\langle 110 \rangle$ -patterned sapphire substrate. Journal of Applied Crystallography, 2013, 46, 1425-1433.	1.9	11
95	Obtaining the structure factors for an epitaxial film using Cu X-ray radiation. Journal of Applied Crystallography, 2013, 46, 1749-1754.	1.9	16
96	Critical role of the sample preparation in experiments using piezoelectric actuators inducing uniaxial or biaxial strains. Review of Scientific Instruments, 2013, 84, 103902.	0.6	7
97	X-ray small-angle scattering from sputtered CeO ₂ /C bilayers. Journal of Applied Physics, 2013, 113, 024301.	1.1	0
98	Co nanocrystals in amorphous multilayers – a structure study. Journal of Applied Crystallography, 2013, 46, 1711-1721.	1.9	5
99	Closely spaced SiGe barns as stressor structures for strain-enhancement in silicon. Applied Physics Letters, 2013, 102, 032109.	1.5	1
100	Lattice strain of hydrogen-implanted silicon: Correlation between X-ray scattering analysis and ab-initio simulations. Journal of Applied Physics, 2013, 113, 153511.	1.1	15
101	Strain relief and shape oscillations in site-controlled coherent SiGe islands. Nanotechnology, 2013, 24, 335707.	1.3	11
102	Strain distribution in Si capping layers on SiGe islands: influence of cap thickness and footprint in reciprocal space. Nanotechnology, 2012, 23, 465705.	1.3	7
103	Scanning tunneling microscopy reveals LiMnAs is a room temperature anti-ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, 112107.	1.5	11
104	Nano-structuring of solid surface by extreme ultraviolet Ar ⁸⁺ laser. Laser and Particle Beams, 2012, 30, 57-63.	0.4	19
105	Tuning luminescence properties of silicon nanocrystals by lithium doping. Journal of Applied Physics, 2012, 112, .	1.1	16
106	Exploiting GISAXS for the Study of a 3D Ordered Superlattice of Self-Assembled Colloidal Iron Oxide Nanocrystals. Crystal Growth and Design, 2012, 12, 5505-5512.	1.4	19
107	Complementary information on CdSe/ZnSe quantum dot local structure from extended X-ray absorption fine structure and diffraction anomalous fine structure measurements. Journal of Alloys and Compounds, 2012, 523, 155-160.	2.8	13
108	Grazing-incidence small-angle X-ray scattering: application to the study of quantum dot lattices. Acta Crystallographica Section A: Foundations and Advances, 2012, 68, 124-138.	0.3	61

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109	Structural and morphological properties of Fe ₂ O ₃ /TiO ₂ nanocrystals in silica matrix. Thin Solid Films, 2012, 520, 4800-4802.	0.8	1
110	Preparation of regularly ordered Ge quantum dot lattices in amorphous matrices. Vacuum, 2012, 86, 733-736.	1.6	6
111	Grazing-incidence x-ray diffraction from GaN epitaxial layers with threading dislocations. Applied Physics Letters, 2011, 98, 021912.	1.5	7
112	X-ray Nanodiffraction on a Single SiGe Quantum Dot inside a Functioning Field-Effect Transistor. Nano Letters, 2011, 11, 2875-2880.	4.5	65
113	Selective coherent x-ray diffractive imaging of displacement fields in (Ga,Mn)As/GaAs periodic wires. Physical Review B, 2011, 84, .	1.1	23
114	Diffuse x-ray scattering from stacking faults in a -plane GaN epitaxial layers. Physical Review B, 2011, 84, .	1.1	20
115	Surface morphology and magnetic anisotropy in (Ga,Mn)As. Applied Physics Letters, 2011, 98, 152503.	1.5	10
116	X-ray characterization of semiconductor nanostructures. Semiconductor Science and Technology, 2011, 26, 064002.	1.0	2
117	Strain field in (Ga,Mn)As/GaAs periodic wires revealed by coherent X-ray diffraction. Europhysics Letters, 2011, 94, 66001.	0.7	22
118	Characterisation of thin LPCVD silicon-rich oxide films. Proceedings of SPIE, 2011, , .	0.8	0
119	A spin-valve-like magnetoresistance of an antiferromagnet-based tunnel junction. Nature Materials, 2011, 10, 347-351.	13.3	485
120	Design of quantum dot lattices in amorphous matrices by ion beam irradiation. Physical Review B, 2011, 84, .	1.1	16
121	Skin Layer of BiFeO_3 Single Crystals. Physical Review Letters, 2011, 106, 236101.	2.9	79
122	Surface characterization of thin silicon-rich oxide films. Journal of Molecular Structure, 2011, 993, 214-218.	1.8	6
123	Molecular beam epitaxy of LiMnAs. Journal of Crystal Growth, 2011, 323, 348-350.	0.7	5
124	Diffusion of Mn interstitials in (Ga,Mn)As epitaxial layers. Physical Review B, 2011, 83, .	1.1	8
125	X-ray interference effects on the determination of structural data in ultrathin La ₂ /3Sr ₁ /3MnO ₃ epitaxial thin films. Applied Physics Letters, 2011, 99, .	1.5	22
126	Demonstration of molecular beam epitaxy and a semiconducting band structure for I-Mn-V compounds. Physical Review B, 2011, 83, .	1.1	55

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127	Strain control of magnetic anisotropy in (Ga,Mn)As microbars. Physical Review B, 2011, 83, .	1.1	13
128	Magnetization reversal assisted by the inverse piezoelectric effect in Co-Fe-B \times ferroelectric multilayers. Physical Review B, 2011, 84, .	1.1	67
129	Tracking defect type and strain relaxation in patterned Ge/Si(001) islands by x-ray forbidden reflection analysis. Physical Review B, 2011, 84, .	1.1	15
130	Electrical Characterization of Ge Nanocrystals in Oxide Matrix. Materials Research Society Symposia Proceedings, 2011, 1305, 1.	0.1	0
131	Kinetic Monte Carlo simulation of quantum-dot nucleation and growth in PbSe/PbEuTe multilayers. Journal of Physics: Conference Series, 2010, 245, 012091.	0.3	0
132	Study of the phase composition of Fe ₂ O ₃ and Fe ₂ O ₃ /TiO ₂ nanoparticles using X-ray diffraction and Debye formula. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1399-1404.	0.8	10
133	Structural and charge trapping properties of two bilayer (Ge+SiO ₂)/SiO ₂ films deposited on rippled substrate. Applied Physics Letters, 2010, 97, 163117.	1.5	17
134	Density of Mn interstitials in (Ga,Mn)As epitaxial layers determined by anomalous x-ray diffraction. Applied Physics Letters, 2010, 97, .	1.5	6
135	Growth of spatially ordered Ge nanoclusters in an amorphous matrix on rippled substrates. Physical Review B, 2010, 82, .	1.1	9
136	Study of Mn interstitials in (Ga, Mn)As using high-resolution x-ray diffraction. Journal of Physics Condensed Matter, 2010, 22, 296009.	0.7	5
137	Self-assembling of Ge quantum dots in an alumina matrix. Physical Review B, 2010, 82, .	1.1	26
138	Generation of an ordered Ge quantum dot array in an amorphous silica matrix by ion beam irradiation: Modeling and structural characterization. Physical Review B, 2010, 81, .	1.1	17
139	X-ray diffuse scattering from threading dislocations in epitaxial GaN layers. Journal of Applied Physics, 2010, 108, 043521.	1.1	38
140	In situ x-ray scattering study on the evolution of Ge island morphology and relaxation for low growth rate: Advanced transition to superdomes. Physical Review B, 2009, 80, .	1.1	17
141	Kinetic Monte Carlo simulation of self-organized growth of PbSe/PbEuTe quantum dot multilayers. Physical Review B, 2009, 80, .	1.1	10
142	Formation of three-dimensional quantum-dot superlattices in amorphous systems: Experiments and Monte Carlo simulations. Physical Review B, 2009, 79, .	1.1	57
143	Self-assembled Mn ₅ Ge ₃ nanomagnets close to the surface and deep inside a Ge _{1-x} Mnx epilayer. Applied Physics Letters, 2009, 95, 023102.	1.5	19
144	Formation of long-range ordered quantum dots arrays in amorphous matrix by ion beam irradiation. Applied Physics Letters, 2009, 95, 063104.	1.5	24

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145	Size and spatial homogeneity of SiGe quantum dots in amorphous silica matrix. Journal of Applied Physics, 2009, 106, 084319.	1.1	11
146	The influence of deposition temperature on the correlation of Ge quantum dot positions in amorphous silica matrix. Nanotechnology, 2009, 20, 085612.	1.3	35
147	Crystal structure of defect-containing semiconductor nanocrystals – an X-ray diffraction study. Journal of Applied Crystallography, 2009, 42, 660-672.	1.9	6
148	X-ray diffraction study of the composition and strain fields in buried SiGe islands. European Physical Journal: Special Topics, 2009, 167, 41-46.	1.2	4
149	Structural Investigations of Core-shell Nanowires Using Grazing Incidence X-ray Diffraction. Nano Letters, 2009, 9, 1877-1882.	4.5	47
150	X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal. Physical Review B, 2009, 79, .	1.1	25
151	Standing-wave-grazing-incidence x-ray diffraction from polycrystalline multilayers. Applied Physics Letters, 2009, 94, .	1.5	3
152	3D SiGe QUANTUM DOT CRYSTALS: STRUCTURAL CHARACTERIZATION AND ELECTRONIC COUPLING. International Journal of Modern Physics B, 2009, 23, 2836-2841.	1.0	5
153	Crystal truncation rod X-ray scattering: exact dynamical calculation. Journal of Applied Crystallography, 2008, 41, 18-26.	1.9	9
154	Structural characterization of self-assembled semiconductor islands by three-dimensional X-ray diffraction mapping in reciprocal space. Thin Solid Films, 2008, 516, 8022-8028.	0.8	8
155	Controlled Aggregation of Magnetic Ions in a Semiconductor: An Experimental Demonstration. Physical Review Letters, 2008, 101, 135502.	2.9	106
156	Standing-wave effects in grazing-incidence x-ray diffraction from polycrystalline multilayers. Journal of Applied Physics, 2008, 103, 033504.	1.1	4
157	Diffuse x-ray scattering from inclusions in ferromagnetic $\text{Ge}_{1-x}\text{Si}_x$ Physical Review B, 2008, 78, .	1.1	14
158	Diffuse x-ray scattering from statistically inhomogeneous distributions of threading dislocations beyond the ergodic hypothesis. Physical Review B, 2008, 77, .	1.1	19
159	Diffuse X-ray scattering from graded SiGe/Si layers. Europhysics Letters, 2008, 82, 66004.	0.7	6
160	Microdiffraction imaging of dislocation densities in microstructured samples. Europhysics Letters, 2008, 82, 56002.	0.7	1
161	X-ray scattering from periodic arrays of quantum dots. Journal of Physics Condensed Matter, 2008, 20, 454215.	0.7	0
162	X-ray in-plane scattering investigation of GaN nanorods. Journal of Applied Physics, 2008, 104, 103504.	1.1	8

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163	In situ investigations of Si and Ge interdiffusion in Ge-rich Si/SiGe multilayers using x-ray scattering. Semiconductor Science and Technology, 2007, 22, 447-453.	1.0	17
164	Shape and composition of buried PbSe quantum dots determined by scanning tunneling microscopy. Applied Physics Letters, 2007, 90, 113119.	1.5	12
165	Local control of magnetocrystalline anisotropy in (Ga,Mn)As microdevices: Demonstration in current-induced switching. Physical Review B, 2007, 76, .	1.1	63
166	Defect Cores Investigated by X-Ray Scattering close to Forbidden Reflections in Silicon. Physical Review Letters, 2007, 99, 225504.	2.9	18
167	InGaN Selfassembled Quantum Dots Investigated By X-Ray Diffraction-Anomalous-Fine Structure Technique. AIP Conference Proceedings, 2007, , .	0.3	2
168	GaMnAs annealing under various conditions: air vs. As cap. AIP Conference Proceedings, 2007, , .	0.3	2
169	Composition and atomic ordering of Ge/Si(001) wetting layers. Thin Solid Films, 2007, 515, 5587-5592.	0.8	6
170	Three-Dimensional Si/Ge Quantum Dot Crystals. Nano Letters, 2007, 7, 3150-3156.	4.5	175
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